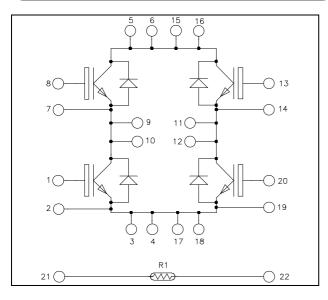


# Full - Bridge NPT IGBT Power Module

 $V_{CES} = 1200V$  $I_{C} = 25A$  @ Tc = 80°C

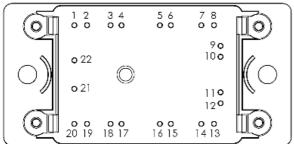


#### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### **Features**

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration



Pins 5/6/15/16 ; 3/4/17/18 ; 9/10 ; 11/12 must be shorted together

#### **Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

### All ratings @ $T_i = 25^{\circ}C$ unless otherwise specified

#### Absolute maximum ratings (per IGBT)

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		1200	V
Ţ	Continuous Collector Current	$T_C = 25^{\circ}C$	40	
$I_{C}$	Continuous Conector Current	$T_C = 80$ °C	25	Α
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	100	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{\mathrm{D}}$	Maximum Power Dissipation	$T_C = 25^{\circ}C$	208	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125$ °C	50A@1150V	

These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



**Electrical Characteristics** (per IGBT)

	Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
	$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V$ ; $V_{CE} = 1200V$				250	μΑ
Ī	V <sub>CE(sat)</sub>	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$	2.5	3.2	3.7	V
			$I_C = 25A \qquad T_j = 125^{\circ}C$		4.0		V	
	$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 1 \text{mA}$		4		6	V
	$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

**Dynamic Characteristics** (per IGBT)

Symbol	Characteristic	Test Conditions	1	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			1650		
Coes	Output Capacitance				250		pF
$C_{res}$	Reverse Transfer Capacitance				110		
$Q_{g}$	Total gate Charge	$V_{GE} = 15V$			160		
$Q_{ge}$	Gate – Emitter Charge	$V_{Bus} = 600V$			10		nC
$Q_{gc}$	Gate – Collector Charge	$I_C=25A$			70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)			60		
$T_{r}$	Rise Time	$V_{GE} = 15V$			50		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 25A$			305		
$T_{\mathrm{f}}$	Fall Time	$R_G = 22\Omega$		30			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	hing (125°C)		60		
$T_{\rm r}$	Rise Time	$V_{GE} = 15V$			50		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 25A$			346		ns
$T_{\mathrm{f}}$	Fall Time	$R_G = 22\Omega$			40		İ
Eon	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 600V$ $I_{C} = 25A$ $R_{G} = 22\Omega$	$T_j = 125$ °C		3.5		Т
$E_{\text{off}}$	Turn-off Switching Energy		$T_j = 125$ °C		1.5		mJ
$I_{sc}$	Short Circuit data	$V_{GE} \le 15V$ ; $V_{Bus} = 900V$ $t_p \le 10 \mu s$ ; $T_i = 125 ^{\circ}C$			160		A
$R_{thJC}$	Junction to Case Thermal Resistance					0.6	°C/W



### Reverse diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions	ī	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			1200			V
$I_{RM}$	Maximum Reverse Leakage Current	V <sub>R</sub> =1200V				100	μΑ
$I_F$	DC Forward Current		$Tc = 80^{\circ}C$		25		A
		$I_F = 25A$			2.6	3.1	
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_F = 50A$			3.2		V
		$I_F = 25A$	$T_j = 125$ °C		1.8		
4	Reverse Recovery Time		$T_j = 25$ °C		320		ns
$t_{rr}$		$I_F = 25A$ $V_R = 667V$	$T_{j} = 125^{\circ}C$		360		
Q <sub>rr</sub>	Reverse Recovery Charge	$di/dt = 200A/\mu s$	$T_j = 25$ °C		480		пC
			$T_{j} = 125^{\circ}C$		1800		пС
$R_{thJC}$	Junction to Case Thermal Resistance					1.4	°C/W

**Temperature sensor NTC** 

Symbol	Characteristic	Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		22		kΩ
$\Delta R_{25}/R_{25}$	Resistance tolerance			5	%
$\Delta \mathrm{B/B}$	Beta tolerance			3	70
B <sub>25/100</sub>	$T_{25} = 298.16 \text{ K}$		3980		K

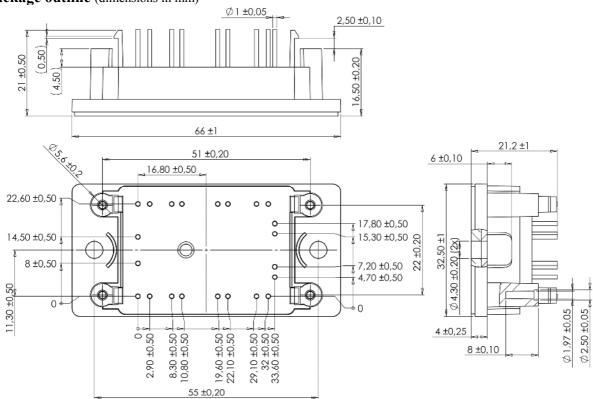
$$R_T = \frac{R_{25}}{\exp\left[B_{25/100}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature R<sub>T</sub>: Thermistor value at T

Thermal and package characteristics

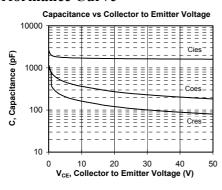
Symbol	Characteristic		Min	Тур	Max	Unit	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range		-40		150		
$T_{STG}$	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					75	g

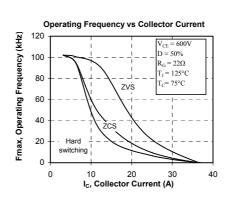


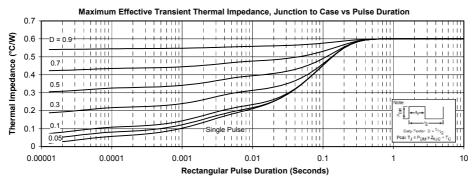
### Package outline (dimensions in mm)



### **Typical Performance Curve**

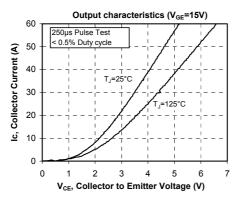


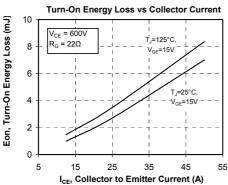


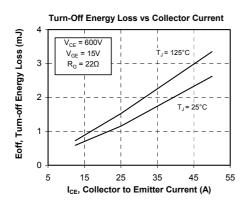


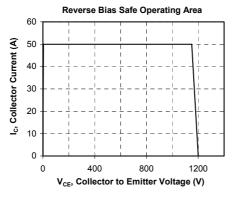
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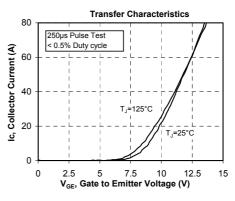


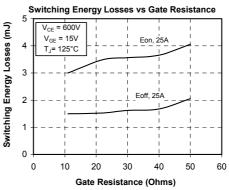


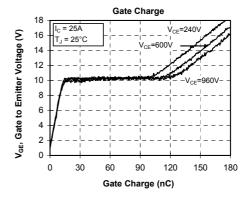






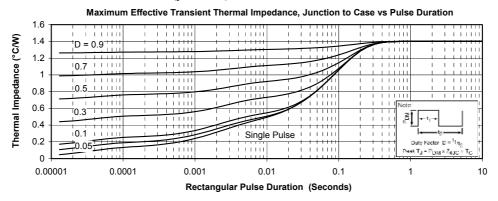


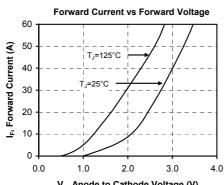






### Typical diode Performance Curve (per diode)





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